L Number	Hits	Search Text	DB	Time stamp
1	644	compensat\$5 near mask	USPAT; US-PGPUB;	2004/02/23 05:14
2	6	(compensat\$5 near mask) and (main near mask)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:17
3	2	mami near miyasaka	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:19
4	214	<pre>(compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:20
5	73	((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:20
6	22	(((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage) and ((second or two or auxiliary or auxilliary) near mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:33
7	576714	(electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:34
8	97280	((electron or charged-particle or (charged adj particle))) and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:34
9	21650	(((electron or charged-particle or (charged adj particle))) and stage) and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:34
10	10268	((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:34
11	2035	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and ((plurality or multiple or two or several) near4 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 05:35
12	204	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:36
13	58	<pre>((((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23
14	55	<pre>(((((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5) and (substrate or wafer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:37

15	54	(((((((electron or charged-particle or	USPAT;	2004/02/23
• •	"	(charged adj particle))) and stage) and	US-PGPUB;	05:37
		mask) and exposure) and (compensat\$5	EPO; JPO;	
	•	near4 mask)) and defect\$5) and	DERWENT;	
		(substrate or wafer)) and (resist or	IBM TDB	
		photoresist or film)		
16	25	((((((((electron or charged-particle or	USPAT;	2004/02/23
10	20	(charged adj particle))) and stage) and	US-PGPUB;	06:10
		mask) and exposure) and (compensat\$5	EPO; JPO;	00110
		near4 mask)) and defect\$5) and	DERWENT;	
		(substrate or wafer)) and (resist or	IBM TDB	
		photoresist or film)) and lens and	1 1211_122	
	[deflect\$4		
17	4	5888682.URPN.	USPAT	2004/02/23
* '	1			05:42
20	3	((compensation adj mask) and	USPAT;	2004/02/23
= 0		(charged-particle or (charged adj	US-PGPUB;	06:10
		particle) or electron)) and (stage near2	EPO; JPO;	
		mask)	DERWENT;	
			IBM TDB	
19	31	(compensation adj mask) and	USPAT;	2004/02/23
		(charged-particle or (charged adj	US-PGPUB;	06:11
		particle) or electron)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	2	("5254438" "5316879").PN.	USPĀT	2004/02/23
	1			06:15
18	99	compensation adj mask	USPAT;	2004/02/23
			US-PGPUB;	06:26
	i		EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	

L	Hits	Search Text	DB	Time stamp
Number	11103			11mc Stamp
1	339	auxiliary near mask	USPAT;	2004/02/23
			US-PGPUB; EPO; JPO;	08:03
			DERWENT;	
			IBM TDB	
2	94	(auxiliary near mask) and (electron or	USPĀT;	2004/02/23
		charged-particle or (charged adj	US-PGPUB;	08:04
ĺ		particle))	EPO; JPO; DERWENT;	
			IBM TDB	
3	42	((auxiliary near mask) and (electron or	USPAT;	2004/02/23
		charged-particle or (charged adj	US-PGPUB;	08:04
		particle))) and stage	EPO; JPO; DERWENT;	
			IBM TDB	
4	12	(((auxiliary near mask) and (electron or	USPAT;	2004/02/23
		charged-particle or (charged adj	US-PGPUB;	09:08
		particle))) and stage) and compensat\$5	EPO; JPO;	
			DERWENT; IBM TDB	
5	10268	(electron or charged-particle or (charged	USPAT;	2004/02/23
		adj particle)) and exposure and mask and	US-PGPUB;	09:09
		stage	EPO; JPO;	
			DERWENT; IBM TDB	
6	3176	((electron or charged-particle or	USPAT;	2004/02/23
	ŧ	(charged adj particle)) and exposure and	US-PGPUB;	09:09
		mask and stage) and ((wafer or substrate)	EPO; JPO;	
		near4 stage)	DERWENT; IBM TDB	
7	1277	(((electron or charged-particle or	USPAT;	2004/02/23
		(charged adj particle)) and exposure and	US-PGPUB;	09:10
		mask and stage) and ((wafer or substrate)	EPO; JPO;	
		near4 stage)) and ((mask or reticle or rectile) near4 stage)	DERWENT; IBM TDB	
8	736		USPAT;	2004/02/23
		(charged adj particle)) and exposure and	US-PGPUB;	09:11
		mask and stage) and ((wafer or substrate)	EPO; JPO;	
		near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or	DERWENT; IBM TDB	
		several or multiple or two) near4 (mask		
		or rectile or reticle))		0004/00/55
9	854	((((electron or charged-particle or (charged adj particle)) and exposure and	USPAT;	2004/02/23
		(charged adj particle) and exposure and mask and stage) and ((wafer or substrate)	US-PGPUB; EPO; JPO;	09.11
		near4 stage)) and ((mask or reticle or	DERWENT;	
		rectile) near4 stage)) and ((plurality or	IBM_TDB	
		several or multiple or two or second) near4 (mask or rectile or reticle))		
10	754		USPAT;	2004/02/23
		(charged adj particle)) and exposure and	US-PGPUB;	09:12
		mask and stage) and ((wafer or substrate)	EPO; JPO;	
		near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or	DERWENT; IBM TDB	
		rectile; hear4 stage;; and ((piurality of several or multiple or two or second)	106-108	
		near4 (mask or rectile or reticle))) and		
		(resist or photoresist)		2004/02/22
11	361	<pre>((((((electron or charged-particle or (charged adj particle)) and exposure and</pre>	USPAT; US-PGPUB;	2004/02/23
	!	mask and stage) and ((wafer or substrate)	EPO; JPO;	05.15
		near4 stage)) and ((mask or reticle or	DERWENT;	
		rectile) near4 stage)) and ((plurality or	IBM_TDB	
		several or multiple or two or second) near4 (mask or rectile or reticle))) and		
		(resist or photoresist)) and stor\$4 and		
		(location or position or address\$2)		

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12	354	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
13	325	<pre>((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
14	98	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:14
15	6	<pre>((((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5) and (non-defect\$5 or nondefect\$5)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
16	49	((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens) and defect\$5) and compensat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:55
17	108	compensation adj (mask or reticle or rectile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:56
18	34	<pre>(compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 10:00
19	20	<pre>((compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))) and exposure</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:57
20	1030	<pre>(electron or charged-particle or (charged adj particle)) and ((wafer or substrate) near stage) and ((reticle or rectile or mask) near stage)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 10:02

(charged adj particle) and ((wafer or substrate) near stage) and ((reticle or rectile) or near (mask or reticle or rectile)) ((two or second) near (mask or reticle) USPAT; US-PGPUB; reference) near2 (mask or reticle or rectile) ((two or second) near (mask or reticle or reference) near2 (mask or reticle) USPAT; US-PGPUB; reference) near2 (mask or reticle) USPAT; US-PGPUB; PGP; JPO; DERWENT; left or rectile) and ((correct\$4 or reference) near2 (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or rectile)) and (non-defective) USPAT; US-PGPUB; PGP; JPO; DERWENT; left or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and exposure and (electron or charged-particle or (charged adj particle)) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and ((mask or reticle) or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and (mask or reticle) or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and (mask or reticle) or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and (mask or reticle) near stage) and (mask or reticle) or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and (mask or reticle) or reticle) near stage)	21				
substrate) near stage) and ((reticle or rectile or mask) near stage)) and ((two or second) near (mask or reticle or rectile) and ((correct\$4 or reference) near2 (mask or reticle or rectile)) and ((non-defective)) 24 2512 ((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage)) and ((mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle))) and (wafer or sample or substrate) near stage)) and ((mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle)) near (staged adj particle)) near stage) and (mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate) near stage)) and ((mask or reticle or rectile) and exposure and (electron or charged-particle) near stage) and ((mask or reticle or rectile) and exposure and (electron or charged-particle) near beam) (((((((two or second) near (mask or reticle or rectile)) and ((wafer or sample or substrate) near stage)) and ((mask or reticle or charged adj particle)) and ((wafer or sample or substrate) near stage)) and (mask or reticle or rectile) and exposure and (electron or charged-particle) or (charged adj particle)) and (wafer or sample or substrate) near stage)) and (mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage)) and (mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) near stage) and (mask or reticle or rectile) and	21	245		USPAT;	2004/02/23
rectile or mask) near stage) and ((two or second) near (mask or reticle or rectile) ((two or second) near (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or rectile) ((two or second) near (mask or reticle or reference) near2 (mask or reticle or rectile)) and (non-defective) USPAT; USP-GPUB; IBM TDB USPAT; USP-GPUB; IBM TDB USPAT; USP-GPUB; IBM TD				1	10:17
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1587			· · · · · · · · · · · · · · · · · · ·	I TRW_IDR	
or rectile) and ((correct34 or reference) near2 (mask or reticle or rectile)) 11 (((two or second) near (mask or reticle or rectile)) and (correct34 or reference) near2 (mask or reticle or rectile)) and (non-defective) 124 2512 ((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) 25 396 (((two or second) near (mask or reticle or rectile) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage) 26 245 ((((two or second) near (mask or reticle or rectile) and exposure and (electron or charged-particle) or (charged adj particle))) and ((wafer or sample or substrate)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle))) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (velectron or charged-particle or (charged adj particle)) and (wafer or sample) (velectron or charged-particle or (charged adj particle)) and (wafer or sampl	2.2	1507	· · · · · · · · · · · · · · · · · · ·	HCDAM.	2004/02/23
reference) near2 (mask or reticle or rectitle) 11	22	1587			
rectile) (((two or second) near (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or rectile)) and (non-defective)				· ·	10:19
11 (((two or second) near (mask or reticle or rectile)) and ((correct\$4 or reference) near2 (mask or reticle or reference) near2 (mask or reticle or rectile)) and (non-defective) 24 2512 ((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) 25 396 (((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and exposure and (electron or charged-particle or (charged adj particle)) and ((wafer or sample or substrate)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substrate) and (clectron or charged-particle or (charged adj particle)) and (wafer or sample or substra				Ī.	
23 11 (((two or second) near (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or reference) near2 (mask or reticle or rectile)) and (non-defective)			Tectife,		
or rectile) and ((corrects4 or reference) near2 (mask or reticle or rectile)) and (non-defective) DERWENT; IBM TDB Contact DERWENT; IBM TDB DERWENT; IBM TD	23	11	((/two or second) near (mask or reticle		2004/02/23
reference) mear2 (mask or reticle or rectile)) and (non-defective) 24	23	11			1
rectile)) and (non-defective) 24			reference) near2 (mask or reticle or		10.21
24 2512 ((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle)) 25 396 (((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and (wafer or sample or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and ((wafer or sample or substrate)) and ((wafer or sample or substrate)) and ((wafer or sample or rectile)) and (wafer or sample or substrate)) and ((wafer or sample or charged-particle)) and ((wafer or sample or rectile)) and (wafer or sample or substrate)) and ((wafer or sample or or charged-particle)) and ((wafer or sample or substrate)) and ((wafer or sample or substrate)) and ((wafer or sample or charged-particle)) and ((wafer or sample or substrate)) and (wafer or sample or substrate) (((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage)) and ((mask or reticle or rectile)) and exposure and ((electron or charged-particle or (charged adj particle)) ((((((two or second) near (mask or rectile or reticle))) and (wafer or sample)) (USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB ((wafer or sample))) ((((((two or second) near (mask or reticle or rectile))) ((((((two or second) near (mask or reticle)))) (((((((two or second) near (mask or reticle)))) ((((((two or second) near (mask or reticle)))) (((((((two or second) near (mask or reticle))))) ((((((two or second) near (mask or reticle))))) ((((((two or second) near (mask or reticle)))) ((((((two or second) near (mask or reticle))))) ((((((two or second))))) ((((two or second))))) (((two or second))) ((two or second)) ((two					
2512 ((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle) (((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle) or (charged adj particle)) and ((wafer or sample or substrate)near stage) (((two or second) near (mask or reticle or rectile)) and ((wafer or sample or substrate)) and ((wafer or sample or substrate)) and ((wafer or sample or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and ((wafer or sample or rectile)) and exposure and (electron or charged-particle) or (charged adj particle)) near stage)) and ((clectron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and ((wafer or sample or substrate)) and (wafer or sample or substrate) near stage)) and ((mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and (wafer or sample or substrate)) and (wafer or sample or substrate) near stage)) and ((clectron or charged-particle)) and (wafer or sample or substrate) near stage)) and ((clectron or charged-particle)) and (wafer or sample or substrate) near stage)) and (wafer or sample or substrate) near stage) and (wafer or sample) 29 185 ((((((two or second) near (mask or reticle))) and (wafer or sample or substrate)) and (wafer or sample or substrate) near stage)) and (wafer or sample) or eticle or rectile) and exposure and (electron or charged-particle or (charged adj particle))) and (wafer or sample or substrate) near stage)) and (wafer or sample) ((clectron or charged-particle or (charged adj particle))) and (wafer or sample or substrate) near stage)) and (wafer or sample) or substrate) near stage) and (wafer or sample) or substrate) near stage		!	lective,,, and (non delective,	· ·	
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charged-particle or (charged adj particle) 25	21	2312		•	
Particle)					
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25 396 (((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage) 26 245 ((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage)) and ((mask or rectile) or rectile) and exposure and (electron or charged-particle or (charged adj particle))) and (wafer or sample or substrate) near stage)) and ((mask or rectile) or rectile) near stage) and ((mask or rectile) or rectile) near stage)) and ((charged adj particle))) and ((wafer or sample or substrate) near stage)) and ((mask or rectile or rectile)) near stage)) and ((charged adj particle)) and (wafer or sample or substrate)) and ((wafer or sample or substrate)) and ((electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and ((electron or charged-particle or (charged adj particle)) and (wafer or sample or substrate)) and ((electron or charged-particle or charged adj particle)) near beam)) and ((electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)) and (wafer or sample or substrate) are rectile or charged-particle or (charged adj particle)) and (wafer or sample or substrate)) and (wafer or sample or substrate)) and (wafer or sample or substrate) and (wa					
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or charged-particle or (charged adj particle))) and ((wafer or sample or substrate) near stage) 245	-		' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	· ·	
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((resist or photoresist or film) with					
(substrate or wafer or sample))) and					
			(lens or (electron near optic\$3))		

30	178	<pre>(((((((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))) and (lens or (electron near optic\$3))) and</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41
31	58	control\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41